TOSHIBA Photocoupler Photo Relay

TLP227GA, TLP227GA-2

Modem

Telecommunications PBXs

The Toshiba TLP227GA series consist of a gallium arsenide infrared-emitting diode optically coupled to a photo-MOSFET in a 4-pin DIP or a 8-pin DIP package, and has a peak off-State voltage of 400 V.

- Normally off function
- TLP227GA : DIP4 (1 form A)
 TLP227GA-2 : DIP8 (2 form A)
- Peak off-state voltage
 - Trigger LED current : 3 mA (max)
- On-state current

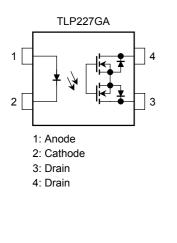
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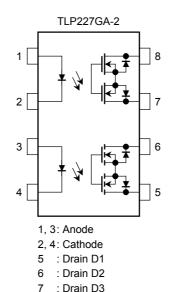
: 120 mA (max)

: 400 V (min)

- On-state resistanceIsolation voltage
- : 35Ω (max)
- : 2500 Vrms (min)

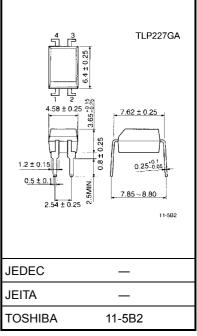
Pin Configuration (top view)



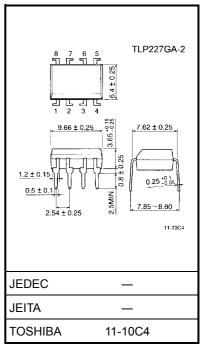


: Drain D4

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Weight: 0.54 g (typ.)

Unit: mm

Maximum Rating (Ta = 25°C)

	C	Characteristic		Symbol	Rating	Unit	
Forward current				lF	50	mA	
	Forward current derating (Ta \ge 25°C)			∆I _F /°C	-0.5	mA/°C	
Led	Peak forward current (100 μs pulse, 100 pps)			I _{FP}	1	А	
	Reverse volt	age		V _R	5	V	
	Junction temperature			Tj	125	°C	
	Off-state out	put terminal vo	tage	V _{OFF}	400	V	
		TLP227GA					
	On-state current	TLP227GA-2	One channel	I _{ON}	120	Ма	
Detector		TLF 227 GA-2	Both channel				
Dete	On-state current rating (Ta≧25°C)	TLP227GA					
		TLP227GA-2	One channel	∆l _{ON} /°C	-1.2	mA/°C	
	Junction tem	perature		Tj	125	°C	
Storage temperature range				T _{stg}	-55~125	°C	
Operating temperature range			T _{opr}	-40~85	°C		
Lea	Lead soldering temperature (10 s)			T _{sol}	260	°C	
lso	lation voltage	(AC, 1 min., R	H. ≦ 60%) (Note 1)	BVS	2500	Vrms	

Note 1: LED pins are shorted together. Detector pins are also shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min	Тур.	Max	Unit
Supply voltage	V _{DD}	_	_	320	V
Forward current	١ _F	5	7.5	25	mA
On-state current	I _{ON}	_	_	100	mA
Operating temperature	T _{opr}	-20		65	°C

Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
	Forward voltage	VF	I _F = 10 mA	1.0	1.15	1.3	V
Led	Reverse current	I _R	V _R = 5 V	_	_	10	μA
	Capacitance	CT	V = 0, f = 1 MHz		30	_	pF
Detector	Off-state current	I _{OFF}	V _{OFF} = 400 V			1	μA
Dete	Capacitance	C _{OFF}	V = 0, f = 1 MHz			_	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Trigger LED current	I _{FT}	I _{ON} = 120 mA	_	1	3	mA
On-state resistance	R _{ON}	$I_{ON} = 120 \text{ mA}, I_F = 5 \text{ mA}$		18	35	Ω

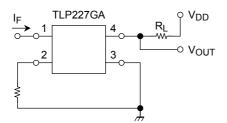
Isolation Characteristics (Ta = 25°C)

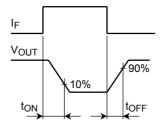
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Capacitance input to output	CS	$V_{S} = 0 V, f = 1 MHz$	—	0.8	_	pF
Isolation resistance	R _S	$V_S = 500 \text{ V}, \text{ R.H.} \le 60\%$	$5 imes 10^{10}$	10 ¹⁴	_	Ω
	BVS	AC, 1 min	2500	_	_	Vrms
Isolation voltage		AC, 1 s (in oil)		5000	_	VIIIS
		DC, 1 min (in oil)	—	5000		Vdc

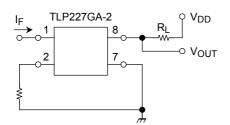
Switching Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Turn-on time	t _{ON}	R _L = 200 Ω	_	_	1	ms
Turn-off time	tOFF	$V_{DD}^{-} = 20 \text{ V}, \text{ I}_{\text{F}} = 5 \text{ mA}$ (Note 2)			1	1113

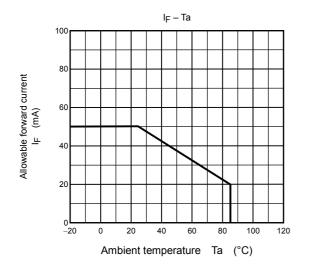
Note 2: Switching time test circuit

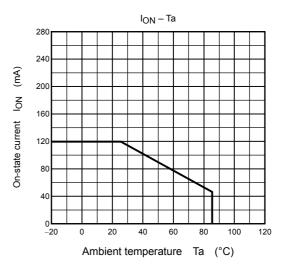


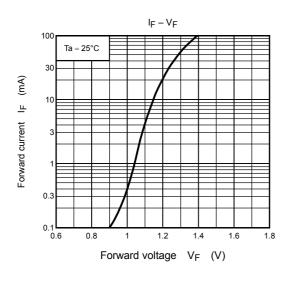


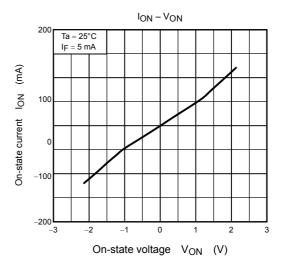


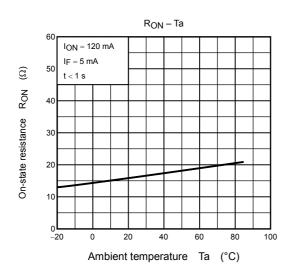
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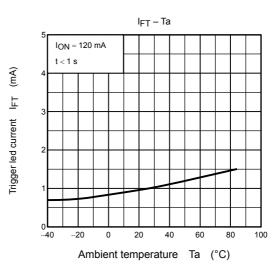




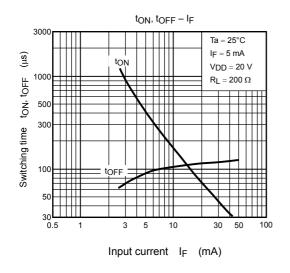


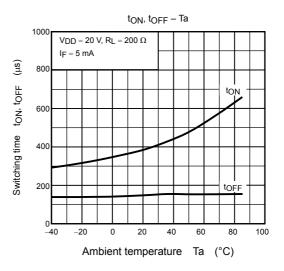


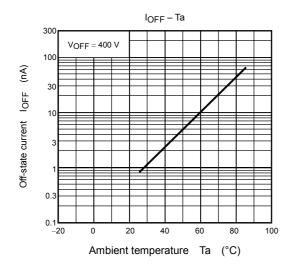




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